

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

MARUYAMA et al.

Application No.: not yet known

Filed: May 29, 2001

Attorney Dkt. No.: 107242-00017

For: WAFER AND EPITAXIAL WAFER, AND MANUFACTURING PROCESSES
THEREFOR

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Date: May 29, 2001

Sir:

Prior to initial examination of the application, please amend the above-identified
application as follows:

Restriction is also not

IN THE CLAIMS:

Please cancel claims 1 - 26 and add the following new claims in their place:

AI -- 27. A silicon wafer, characterized in that an attached boron amount on a
surface of the silicon wafer is 1×10^{10} atoms/cm² or less.

28. A silicon wafer, characterized in that an increment of a boron
concentration in a surface layer down to a depth of 0.5 μ m relative to a boron